			DB	Time stamp
Number	Hits	Search Text	USPAT;	2002/10/21 12:56
-	455704	diode	US-PGPUB;	
			EPO; JPO;	
	ļ		DERWENT	
			USPAT;	2002/10/21 12:56
-	23957	Schottky	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
			USPAT;	2002/10/21 12:57
-	58252	MOS adj transistor	US-PGPUB;	
	00212		EPO; JPO;	
			DERWENT	1
			USPAT;	2002/10/21 12:57
-	153048	silicon near5 substrate	US-PGPUB;	
	155040		EPO; JPO;	
			DERWENT	
			USPAT;	2002/10/21 12:59
-	45236	silicide	US-PGPUB;	2002, 201
	45250	31110240	EPO; JPO;	
			DERWENT	2002/10/21 13:01
-	156	diode and Schottky and (MOS adj	USPAT;	2002/10/21 10
	156	transistor) and (silicon near5 substrate)	US-PGPUB;	1
	1	and silicide	EPO; JPO;	
			DERWENT	2002/10/21 13:03
-		(titanium tungsten cobalt platinum) near5	USPAT;	2002/10/21 13:0
	3	(titanium tungsten cozurt r	US-PGPUB;	
		silicode	EPO; JPO;	
	1		DERWENT	2002/10/21 13:0
		(titanium tungsten cobalt platinum) near5	USPAT;	2002/10/21 13.0
	17605	(titanium tungsten cobart prasi-	US-PGPUB;	
		silicide	EPO; JPO;	
			DERWENT	12.0
		and (MOS add	USPAT;	2002/10/21 13:0
-	98	diode and Schottky and (MOS adj transistor) and (silicon near5 substrate)	US-PGPUB;	1
		transistor) and (Silicon hears substitute)	EPO; JPO;	1
		and ((titanium tungsten cobalt platinum)	DERWENT	
		near5 silicide)	USPAT;	2002/10/21 13:0
	1 3	diode and Schottky and (MOS adj	US-PGPUB;	
			EPO; JPO;	
	1		DERWENT	
		and (IIC (Integrated and	32	
		-ii+\\ nearb (Card Module//	USPAT;	2002/10/21 13:1
_	7.		US-PGPUB;	
		I and (SILICON REGIS SUBSCIACO)	EPO; JPO;	
			DERWENT	
		and ((titanium tungsten coburt protection near5 silicide)) and (IC (integrated adj	DELVIENT	_
		circuit))		